

GL4401

NPN EPITAXIAL PLANAR TRANSISTOR

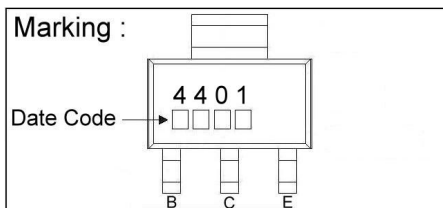
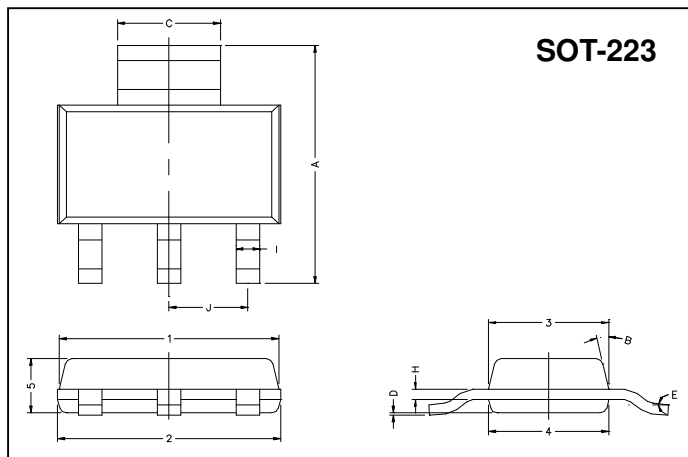
Description

The GL4401 is designed for general purpose switching and amplifier applications.

Features

- Complementary to GL4403
- High Power Dissipation: 1500mW at 25°C
- High DC Current Gain: 100-300 at 150mA

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13 TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage at Ta=25°C	V _{CB0}	60	V
Collector to Emitter Voltage at Ta=25°C	V _{CE0}	40	V
Emitter to Base Voltage at Ta=25°C	V _{EB0}	5	V
Collector Current at Ta=25°C	I _C	600	mA
Total Power Dissipation at Ta=25°C	PD	1.5	W

Characteristics at Ta = 25°C

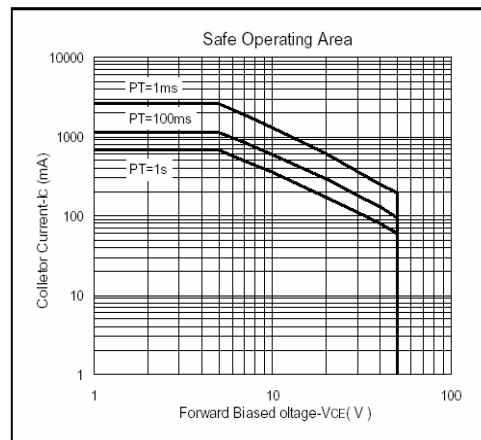
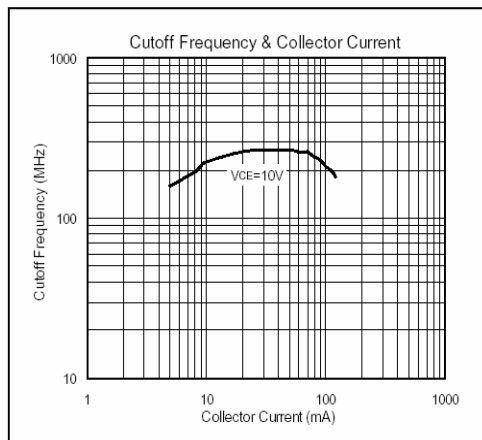
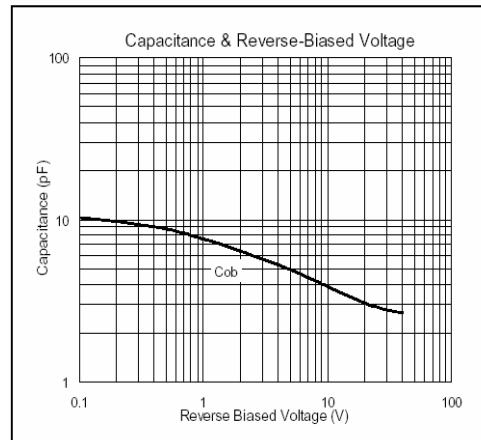
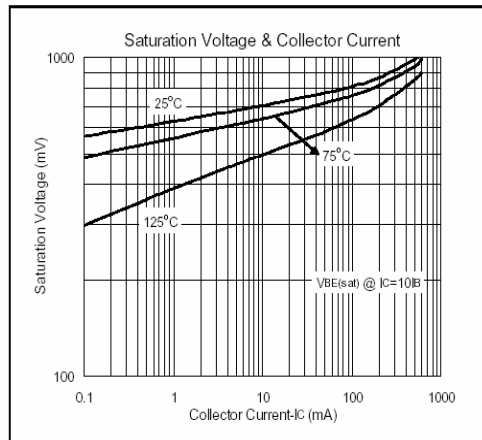
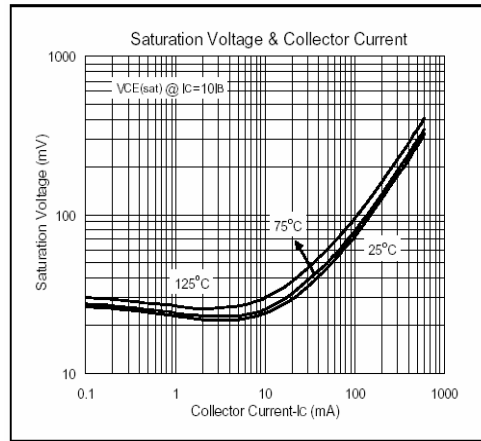
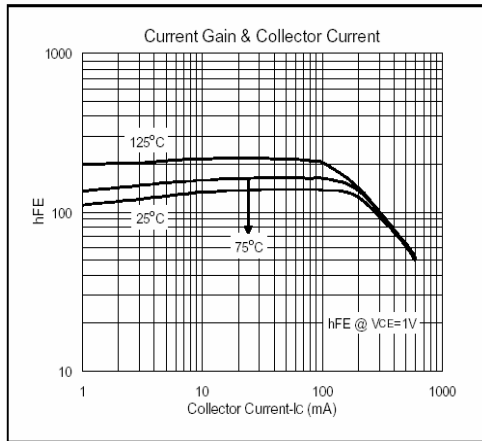
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	60	-	-	V	I _C =100μA
BV _{CE0}	40	-	-	V	I _C =1mA
BV _{EB0}	5	-	-	V	I _E =10μA
ICEX	-	-	100	nA	V _{CE} =35V, V _{BE} = 0.4V
*V _{CE(sat)1}	-	-	400	mV	I _C =150mA, I _B =15mA
*V _{CE(sat)2}	-	-	750	mV	I _C =500mA, I _B =50mA
*V _{BE(sat)1}	750	-	950	mV	I _C =150mA, I _B =15mA
*V _{BE(sat)2}	-	-	1.2	V	I _C =500mA, I _B =50mA
*h _{FE1}	20	-	-		V _{CE} =1V, I _C =0.1mA
*h _{FE2}	40	-	-		V _{CE} =1V, I _C =1mA
*h _{FE3}	80	-	-		V _{CE} =1V, I _C =10mA
*h _{FE4}	100	-	300		V _{CE} =1V, I _C =150mA
*h _{FE5}	40	-	-		V _{CE} =2V, I _C =500mA
f _T	250	-	-	MHz	V _{CE} =10V, I _C =20mA, f=100MHz
C _{ob}	-	-	6.5	pF	V _{CB} =5V, f=1MHz

Classification Of hFE4

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Rank	A	B
Range	100-210	190-300

Characteristics Curve



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